FAST HIGH VOLTAGE TRANSISTOR SWITCHES

This new generation of BEHLKE high voltage switching modules utilize an advanced MOSFET technology with very low on-resistance, the so called Trench FET technology. The switching speed of those modern FET is slightly slower than that of a classical power FET, but is still much faster than that of any IGBT, which is preferably used to achieve low turn-on losses. The new MOSFET switches of series HTS-B combine very low dynamic switching losses with moderate turn-on losses and are a serious alternative to IGBT switches. Another important advantage compared to the fault sensitive IGBT is the positive temperature coefficient of the on-resistance, which makes the switch short circuit proof within the thermal limits. Furthermore overvoltage transients as well as voltage reversal respectively current reversal is less dangerous to MOSFET's than to IGBT's. Insofar these switching modules are well suitable for applications with high demands on operational safety even under worst conditions.

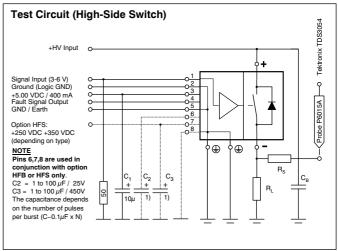
The switching modules incorporate all features of the well known HTS switch family: Easy handling, high reliability, low jitter and reproducible switching behaviour.

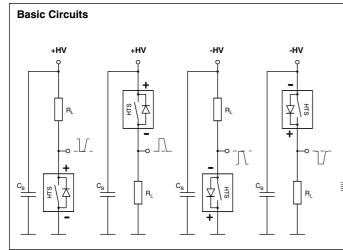
The switch is turned on by a positive going signal of 3 to 6 volts amplitude, provided the auxiliary power supply is permanently connected to the +5.00 VDC input. The on-time may simply be varied between 250 ns and infinity by the input control pulse width. An interference-proof driver circuit provides signal conditioning, auxiliary voltage monitoring, frequency limitation and temperature protection. In case of any false operating condition the switches turn off immediately and a fault signal is generated (TTL level). The high frequency burst operation (>10 pulses/100 μ s) requires the option HFB (connection of external buffer capacitors at the driver). For operation at higher frequencies than specified under f_(max) the option HFS must be used. In that case an internal DC/DC converter must be supported by an external supply of +250 VDC to +350 VDC (\pm 5%, approx. 2-10 Watts depending on switching frequency and type of switching module).

Due to the high galvanic isolation the switches may simply be operated also in floating set-up's or in high-side circuits. Several housing options are available to meet individual constructional and power requirements. The standard plastic housing is used in low frequency applications with low average power dissipation. The plastic modules can additionally be fitted with non-isolated cooling fins (available as options CF, CF-X2 and CF-X3), which improves the max. Continuous Power Dissipation $P_{\text{d(max)}}$ by approx. factor 10 with forced air (>4m/s) or by factor 50, if the switching modules are immersed in isolating cooling liquids (e.g. GALDEN HT135, flow rate >0.1m/s, standard cooling fins). Another cooling method is given by the use of the grounded cooling flange (option GCF and GCF-X2). In conjunction with an optional water cooling plate or any other high performance heatsink, maximum power dissipations in the range of 2 to 6 kW are possible, with larger customized cooling flanges even up to 10 kW.

The modules can be installed on a printed circuit board, but if operated under air conditions, the use of option PT-HV (pigtails for HV connection) is recommended, in order to ensure a sufficient creepage distance according to industrial standards. For detailed design recommendations please refer to the general instructions for use.

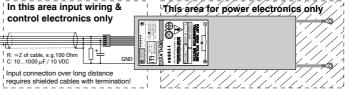






Important EMC Design Hints

- Keep the wiring as short as possible and avoid large induction loop areas of the peak current carrying lines; the forward and return lines should be installed as closely as possible together. Control and power circuit must not be mixed. Always keep the transformer principle in mind!
- Use shielded leads at the control side to minimize noise induction. Low impedance drivers
 with 5 Volt output swing (into 50 Ohm) are required for driving long pulse transmission lines.
 Signal transmission lines must be terminated properly (e.g. by 50 Ohm). The auxiliary power
 supply must be well decoupled by a sufficient buffer capacitor.
- This high speed switching module can generate extreme di/dt's and dv/dt's. Therfore it is not useful to operate the switch and its peripheric components without a shielded housing. Other electronics including power supplies (!) may be disturbed. Please note your local EMC / EMI regulations. Please also see our option offers for possible EMC / EMI relevant modifications.





TECHNICAL DATA

Specification	Symb.	Condition / 0	Condition / Comment HTS:		151-12-B	181-12-B	211-12-B	Unit
Maximum Operating Voltage	$V_{O(max)}$	I _{off} < 60 μADC		15	18	21.6	kVDC	
Minimum Operating Voltage	$V_{O(min)}$	Increased $t_{r(on)}$ and $t_{r(off)}$ below 0.1x $V_{O(max)}$				0		kVDC
Typical Breakdown Voltage	V _{br}	$I_{\text{off}} > 1 \text{mADC}, T_{\text{case}} = 75 \text{ °C}$			15.7	18.9	22.7	kVDC
Galvanic Isolation	VI	Continuously		housing / PCB attachment		25		
Maximum Peak Current	- 1			T-HV, pigtails for HV		40		
			-	T-HV + Option ISO-80 1)		80		kVDC
	1	T _{case} = 25°C		μs, duty cycle <1%		125		KVDO
	I _{P(max)}			ns, duty cycle <1%		67		
		$T_{fin} = 75^{\circ}C^{*}$	-	• •				400
Mariana Oralina and		*measured at base		ns, duty cycle <10%		52		ADC
Maximum Continuous Load	I _L	T _{case} = 25°C		d plastic case		3		
Current		T _{flange} =25°C	-	CF, fins in air >4m/s		10		
		$T_{fin} = 75^{\circ}C^{*}$		F, in Galden® >0.1m/s		12.9		
		*measured at base		F, grounded cooling flange		20.4		ADC
Static On-Resistance	R _{stat}	T _{case} = 25°C	0.1 x I _{P(m}		2.4	3	3.4	
			1.0 x I _{P(m}		6	7.4	8.6	Ω
Maximum Off-State Current	I _{off}	$0.8xV_{O,}$ $T_{case}\!\!=\!\!75^{\circ}C,$ $<\!\!5\mu A$ leakage optionally available				50		μADC
Turn-On Delay Time	t _{d(on)}	@ I _{P(max)}			170	180	200	ns
Typical Turn-On Rise Time	t _{r(on)}	0.1 x V _o , 0.1 x	I _{P(max)}		12	13	13	
,,	, ,	0.5 x V _O , 0.1 x			15	18	20	
		0.8 x V _o , 0.1 x			22	26	31	
		0.8 x V _o , 1.0 x			47	51	56	ns
Typical Turn-Off Rise Time	t _{r(off)}	0.8 x V _O , 0.1x I _{P(max)} , resistive load, 10-90%				60		ns
Minimum On-Time		Lower t _{on(min)} on request				200		ns
Maximum On-Time	t _{on(min)}	Please note possible P _{d(max)} limitations				∞		110
Switch Recovery Time	t _{on(max)}					500		no
	t _{rc}	t _{rc} = minimum pulse spacing						ns
Typical Turn-On Jitter	t _{j(on)}	V _{aux} / V _{tr} = 5.0 VDC, fixed switching frequency			500		ps	
Max. Switching Frequency	$f_{(max)}$	T _{case} = 25°C		I, safety turn-off @1.5x f _(max)	2	1.8	1.5	
				IFS, please consult factory	max. 80	max. 80	max. 80	kHz
Maximum Burst Frequency	f _{b(max)}	Use option HFB for >5 pulses within100 μs			2		MHz	
Maximum Continuous Power	$P_{\text{d(max)}}$	$T_{case} = 25^{\circ}C$			22	26	32	
Dissipation		T _{flange} =25°C	FC Option	on CF, fins in air >4m/s	240	288	346	
		$T_{fin} = 75^{\circ}C^{*}$	Option C	CF, in Galden® >0.1m/s	1000	1200	1440	
		*measured at base	Opt. GC	F, grounded cooling flange	2500	3000	3600	Watts
Linear Derating		T _{case} = 25°C	Standard	plastic case incl. option	0.44	0.52	0.64	
		T _{flange} =25°C	FC Option	on CF, fins in air >4m/s	4.8	5.76	6.92	
		$T_{fin} = 75^{\circ}C^{\star}$	Option C	F, in Galden® >0.1m/s	20	24	28.8	
		*measured at base	-	F, grounded cooling flange	50	60	72	W/K
Operating Temperature Range	To		ended range on request, safety turn-off @ 77°C			-4075		°C
Storage Temperature Range	T _{ST}	Extended range on request, safety tarm on @ 77 0				-5090		°C
Natural Capacitance	C _N	Capacitance between switch poles at V _{O(max)}		20	25	30	pF	
Coupling Capacitance	C _C	HV side to		d devices	39	47	56	Pi
Diode Reverse Recovery Time	Oc	control / GND		F, grounded cooling flange	239	287	344	pF
	1				209		044	•
		I _F = 10 A, T _{case} =		MOSFET parasitic diode	07	500		ns
Diode Forward Voltage Drop	V _F	I _F = 10 A, T _{case} =		MOSFET parasitic diode	27	41	53	VDC
Auxiliary Supply Voltage	V _{aux}	Stabilized to ± 2%, safety		y turn-off below 4.75 VDC		5.0		VDC
Auxiliary Supply Current	l _{aux}	@ f _{max}				600		mADC
Control Signal Voltage	V_{tr}	> 3VDC recommended				2-6		VDC
Fault Signal Output		TTL, short circuit proof, L=Fault (=safety turn-off)				l= 4 V, L= 0.5	V	VDC
Dimensions	LxWxH	Standard plas			212x70x35	263x70x35	263x70x35	
		Option FC, flat			212x70x19	263x70x19	263x70x19	
		Option CF, nor	n-isolated	cooling fins, standard size	212x70x70	263x70x70	263x70x70	
		Option GCF, gr		-	252x120x45	312x120x45	312x120x45	mm ³
Weight		Standard plas		<u> </u>	750	1020	1050	
5		Option FC, flat			440	590	610	
				cooling fins, standard size	1125	1560	1590	
		Option GCF, gr		<u> </u>	2700	3420	3450	a
				available in other sizes for h			3450	g

Notes: 1) Not available in connection with Option GCF. 2) Also available in other sizes for higher or lower P_{d(max)}. Please consult factory.

Ordering Information

HTS 151-12-B Transistor switch, 15 kVDC, 125 Amps. Option ISO-80 Increased isolation voltage, 80 kVDC isolation Option SPT-C Shielded pigtail for control connection (LEMO miniature plug) HTS 181-12-B Transistor switch, 18 kVDC, 125 Amps. HTS 211-12-B Transistor switch, 21 kVDC, 125 Amps. Option PT-HV Pigtails for HV connection (instead of bottom screw terminals) Option HFB High frequency burst Option UL-94 Flame-retardant casting resin according to UL94-V0 Option HFS **Option FC** High frequency switching (pls. consult factory) Flat plastic case, module height reduced to 19 mm Option LP **Option CF** Non-isolated cooling fins, standard size, 35 mm height Low pass filter at control input **Option S-TT** Soft transition time for simplified EMC design **Option GCF** Grounded cooling flange, direct attachment to heat sink